

MBR1635 THRU MBR1660

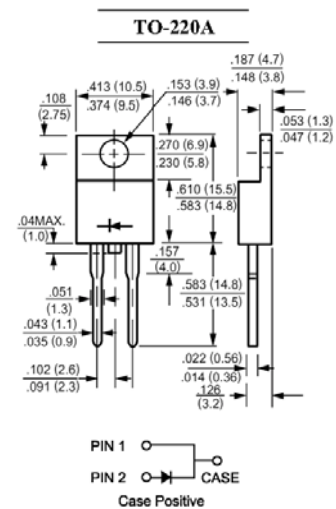
SCHOTTKY BARRIER RECTIFIER Reverse Voltage - 35 to 60 V Forward Current - 16 A

Features

- Metal silicon junction, majority carrier conduction
- Guard ring for overvoltage protection
- High current capability
- Low power loss, high efficiency
- Low forward voltage drop
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications

Mechanical Data

- Case: Molded plastic, TO-220A
- Epoxy: UL 94V-0 rate flame retardant
- Terminals: Leads solderable per MIL-STD-202 Method 208 guaranteed
- Polarity: As marked
- Mounting position: Any



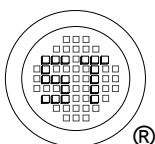
Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Parameter	Symbols	MBR1635	MBR1645	MBR1650	MBR1660	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	35	45	50	60	V
Maximum RMS Voltage	V_{RMS}	24	31	35	42	V
Maximum DC Blocking Voltage	V_{DC}	35	45	50	60	V
Maximum Average Forward Rectified Current $T_C = 125\text{ }^\circ\text{C}$	$I_{F(AV)}$	16				A
Peak Repetitive Forward Current at $T_C = 125\text{ }^\circ\text{C}$ (Rated V_R , Sq. Wave, 20 KHz)	I_{FRM}	32				A
Peak Forward Surge Current, 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I_{FSM}	150				A
Peak Repetitive Reverse Current at $t_p = 2\text{ }\mu\text{s}$, 1 KHz	I_{RRM}	1		0.5		A
Maximum Forward Voltage ¹⁾ at $I_F = 16\text{ A}$, $T_C = 25\text{ }^\circ\text{C}$ at $I_F = 16\text{ A}$, $T_C = 125\text{ }^\circ\text{C}$	V_F	0.63		0.75		V
Maximum Reverse Current at Rated DC Blocking Voltage at $T_C = 25\text{ }^\circ\text{C}$ at $T_C = 125\text{ }^\circ\text{C}$	I_R	0.2		1		mA
40				50		
Voltage Rate of Change (Rated V_R)	dv/dt	10,000				V/ μs
Typical Thermal Resistance	$R_{\theta JC}$	1.5				$^\circ\text{C}/\text{W}$
Operating Temperature Range	T_J	- 55 to + 150				$^\circ\text{C}$
Storage Temperature Range	T_S	- 55 to + 175				$^\circ\text{C}$

¹⁾ Pulse test: 300 μs pulse width, 1% duty cycle



SEMTECH ELECTRONICS LTD.

(Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



ISO/TS 16949 : 2002 Certificate No. 05103
ISO 14001:2004 Certificate No. 7116
ISO 9001:2000 Certificate No. 0506098

Dated : 29/08/2007 H

MBR1635 THRU MBR1660

Fig. 1 - Forward Current Derating Curve

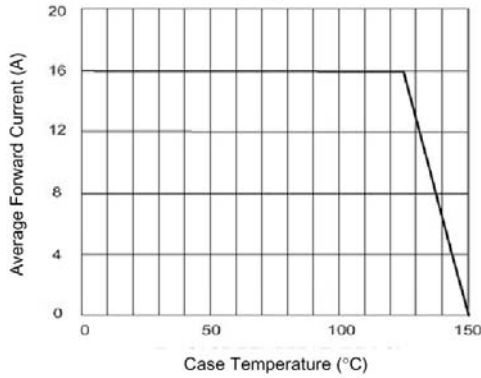


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current

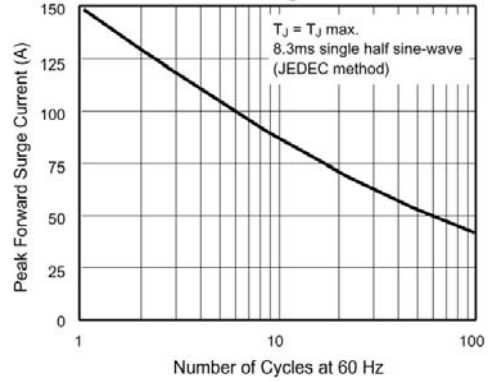


Fig. 3 - Typical Instantaneous Forward Characteristics

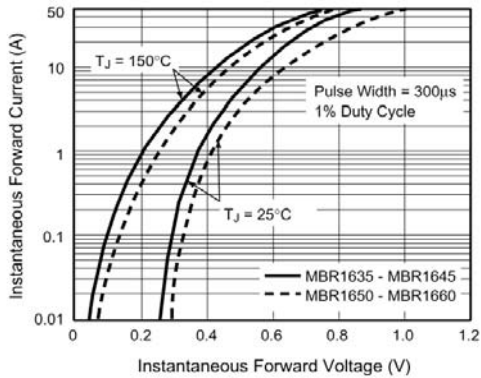


Fig. 4 - Typical Reverse Characteristics

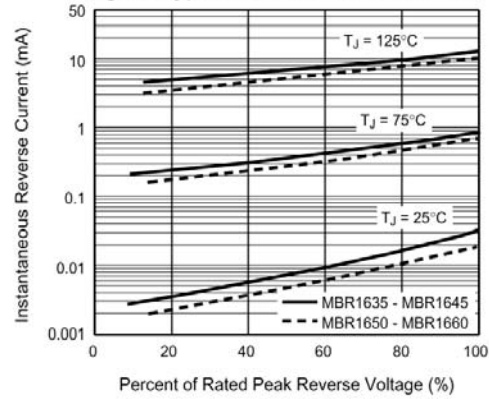


Fig. 5 - Typical Junction Capacitance

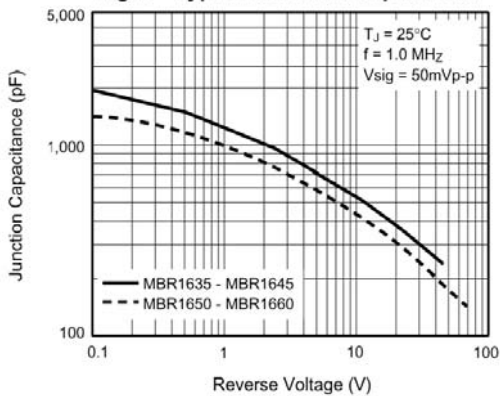
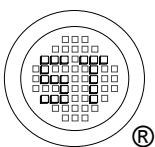
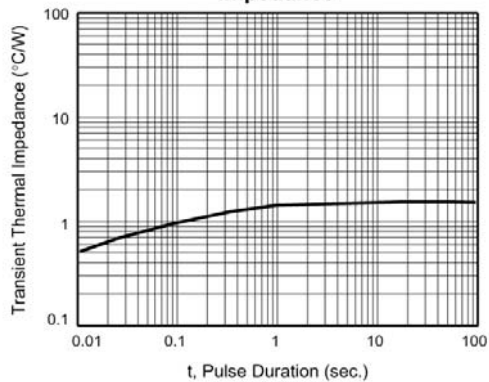


Fig. 6 - Typical Transient Thermal Impedance



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